

PDTA123EU,115 Datasheet



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DiGi Electronics Part Number PDTA123EU,115-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PDTA123EU,115

Description TRANS PREBIAS PNP 50V SOT323

Detailed Description Pre-Biased Bipolar Transistor (BJT) PNP - Pre-Biase

d 50 V 100 mA 200 mW Surface Mount SOT-323



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PDTA123EU,115	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	2.2 kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
2.2 kOhms	30 @ 20mA, 5V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
150mV @ 500μA, 10mA	1μΑ
Power - Max:	Grade:
200 mW	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
SC-70, SOT-323	SOT-323
Base Product Number:	
PDTA123	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA123E series PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Product data sheet Supersedes data of 2004 Apr 07



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	2.2	-	kΩ
R2	bias resistor	2.2	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TVDE NUMBER	PAC	(AGE	MARKING CORE	NPN COMPLEMENT	
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE		
PDTA123EE	SOT416	SC-75	5C	PDTC123EE	
PDTA123EEF	SOT490	SC-89	6C	PDTC123EEF	
PDTA123EK	SOT346	SC-59	42	PDTC123EK	
PDTA123EM	SOT883	SC-101	F7	PDTC123EM	
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES	
PDTA123ET	SOT23	ı	*21 ⁽¹⁾	PDTC123ET	
PDTA123EU	SOT323	SC-70	*42 ⁽¹⁾	PDTC123EU	

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Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TVDE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA123ES	1 R1 R2 3 MAM338	1 2 3	base collector emitter
PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU	3 1 R1 R2 Top view MDB271	1 2 3	base emitter collector
PDTA123EM	2 R1 3 Bottom view ADB267	1 2 3	base emitter collector

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PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE							
ITPE NUMBER	NAME	VERSION						
PDTA123EE	_	plastic surface mounted package; 3 leads	SOT416					
PDTA123EEF	_	plastic surface mounted package; 3 leads	SOT490					
PDTA123EK	_	plastic surface mounted package; 3 leads	SOT346					
PDTA123EM	_	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883					
PDTA123ES	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54					
PDTA123ET	_	plastic surface mounted package; 3 leads	SOT23					
PDTA123EU	_	plastic surface mounted package; 3 leads	SOT323					

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		_	-12	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	PARAMETER CONDITIONS			MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	_	_	-2	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -20 \text{ mA}$	30	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	_	-1.2	-0.5	V
$V_{i(on)}$	input-on voltage	$I_C = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2	-1.6	_	V
R1	input resistor		1.54	2.2	2.86	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	_	_	3	pF

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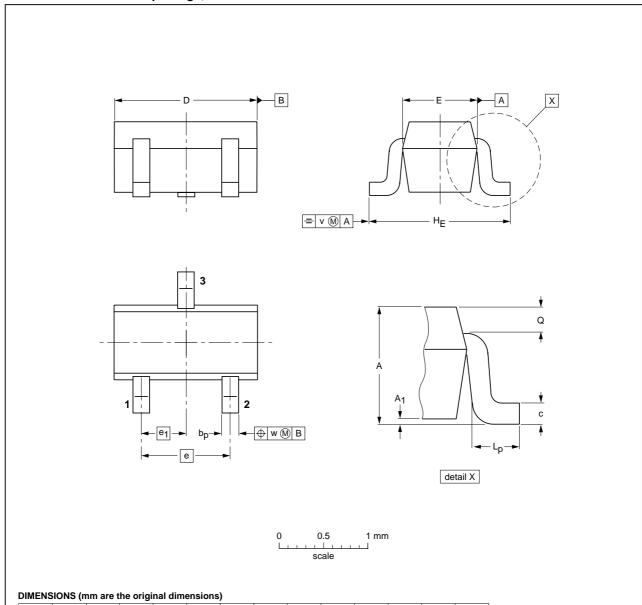
PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT416



UNIT	A	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	٧	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	REFERENCES			ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT416			SC-75			04-11-04 06-03-16	

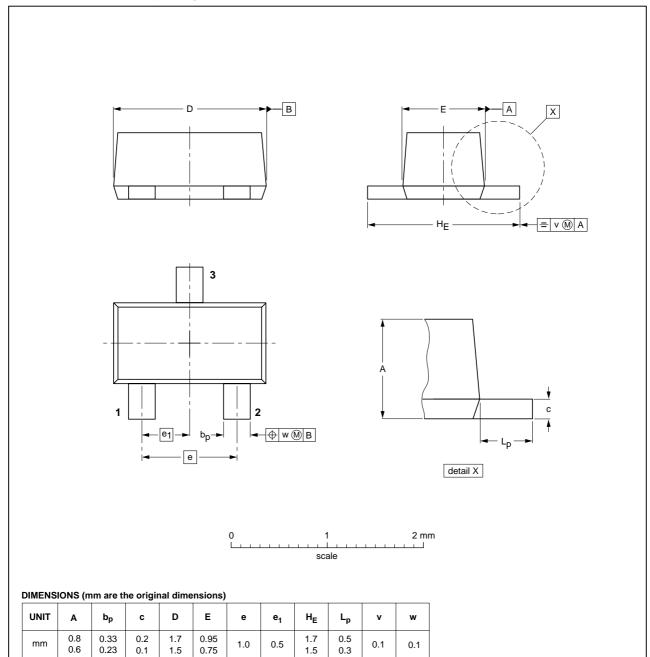
6

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT490



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT490			SC-89		05-07-28 06-03-16

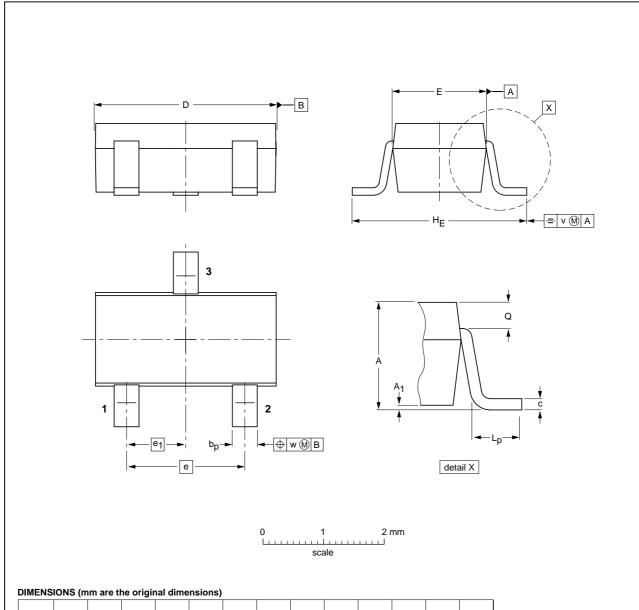
7

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT346



UNIT	Α	A ₁	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A			04-11-11 06-03-16	

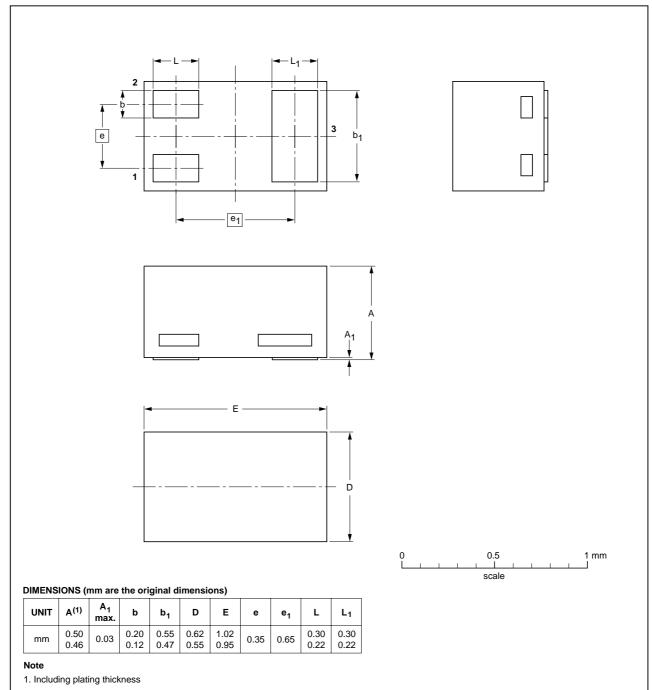
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PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



OUTLINE		EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT883			SC-101			03-02-05 03-04-03	

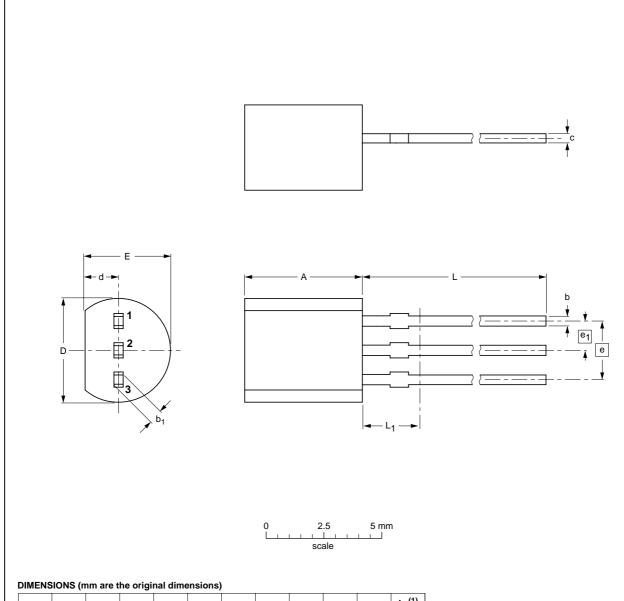
9

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			-04-06-28 04-11-16	

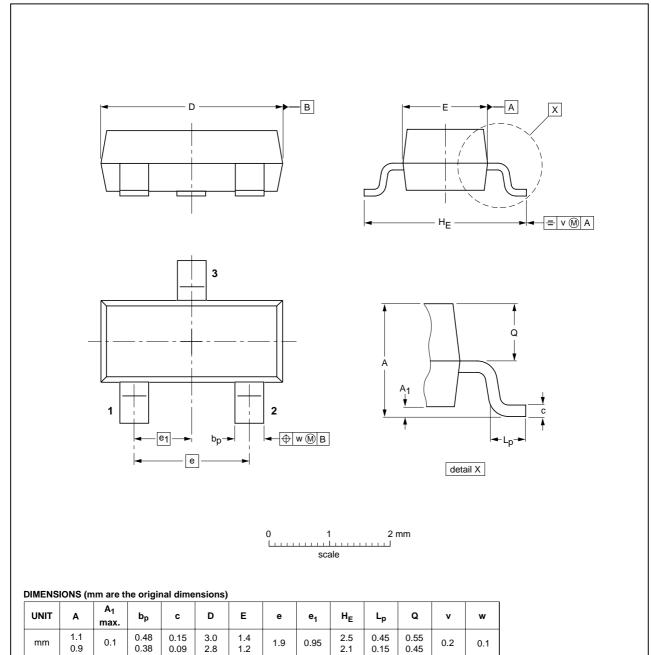
2004 Aug 02 10

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT23



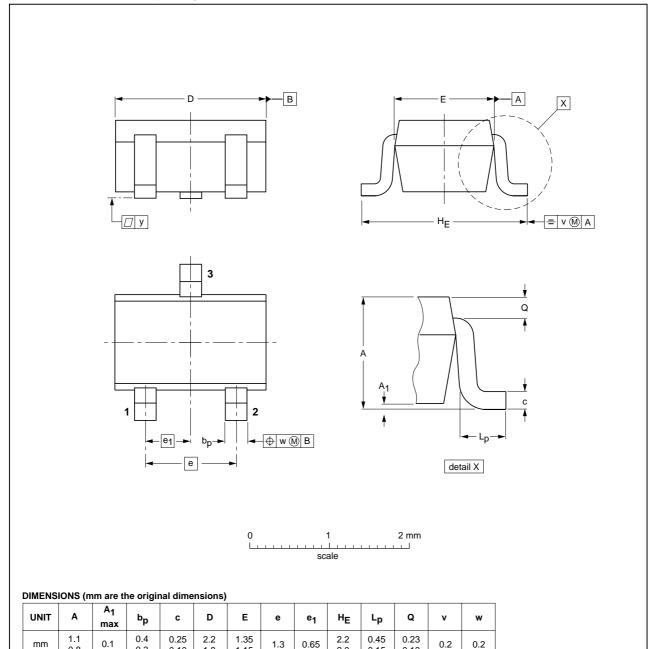
OUTLINE		REFER	EUROPEAN	ICCUE DATE		
VERSION IEC		JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04 06-03-16

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT323



OUTLINE		EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	JEITA	PROJECTION		ISSUE DATE	
SOT323			SC-70			-04-11-04 06-03-16	

0.3

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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